

Docket No. BU9-97-149

In the Claims

Please cancel claims 30-45 in light of the restriction requirement made by the Examiner.

Please substitute the following amended claims for the pending claims having the same number:

B1
Claim 1. A method for forming an interconnection between a storage capacitor and a transfer device in a memory cell, the method comprising the steps of:

- a) forming a capacitor having a lip extending over a top surface of a substrate; and
- b) diffusing dopant from the lip into the top surface of the substrate, the diffusing dopant forming a surface strap in the substrate, the surface strap providing a connection between the capacitor and the transfer device.

B2
Claim 17. A method for forming a connection between a capacitor and a transfer device on a semiconductor substrate having a top surface, the method comprising the steps of:

- a) forming a first layer on the semiconductor substrate;
- b) etching an oversized capacitor opening in the first layer;
- c) forming a sidewall spacer on the sidewalls of the oversized capacitor opening;
- d) etching a capacitor trench in the semiconductor substrate using said sidewall spacer and said first layer as a mask, said capacitor trench having a top edge at the top surface of said semiconductor substrate;
- e) depositing capacitor fill material in said capacitor trench, said capacitor fill material extending over said capacitor trench top edge to form a lip of capacitor fill material on said top surface of said semiconductor substrate; and
- f) diffusing dopants from said capacitor fill material into said semiconductor substrate from said lip of capacitor fill material, the diffusing dopant forming a surface strap in